Texas Photonics, Inc.

TXPI 1034
NPN Phototransistor
0.017" Square Active Area

DESCRIPTION

This is a Silicon Phototransistor designed for applications requiring medium gain and a wide viewing angle.

FEATURES

- ❒ Medium Gain, typically 500 Hfe
- ❒ Sensitivity range 400-1000 nm
- ❒ High Reliability
- ❒ Hermetic Package

ABSOLUTE MAXIMUM RATINGS

- ❒ Storage temperature..... -55°C to +125°C
- ❒ Case operating temperature... -40°C to +85°C
- ❒ Lead solder temperature..... 260°C, 10 seconds
- ❒ Supply Voltage..... +30 Volts

OPERATING CONDITIONS

- ❒ Supply Voltage..... +0 to +30 Volts

PRELIMINARY

OUTLINE DIMENSIONS

All dimensions are in inches (except as noted)

Pinout : 1. Emitter, 2. Base, 3. Case (Collector)

ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Collector Emitter Breakdown	I_C = 100 μ_A, I_B = 0	BVCEO	60			Volts
Emitter - Collector Breakdown	I_E = 100 μ_A, I_B = 0	BVECO	5			Volts
Collector Dark Current	VCE = 20V, H = 0 mW/cm2	ICEO			100	nA
Collector-Emitter Saturation	I_C = 2 mA, I_B = 100 μ_A	VCESAT			0.3	Volts
Response Time	10%-90%, IC = 1 mA VCE = 5 V, RL=1000 Ω	t_r t_f		15 15		µsec µsec
Current Gain	IC = 2 mA, VCE = 5 V	H_{fe}	200	500		

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